TEXAS INSTRUMENTS

JAJSGR6C – FEBRUARY 2003 – REVISED DECEMBER 2018

SN74CB3T3125 クワッドFETバス・スイッチ 2.5V、3.3V低電圧バス・スイッチ、5V耐圧レベル・シフタ付き

1 特長

- 出力電圧変換がV_{CC}に追従
- すべてのデータI/Oポートで混在モード信号動作をサポート
  - 3.3VのV_{CC}の場合、5V入力を3.3V出力にレベル・シフト
  - 2.5VのV_{CC}の場合、5V/3.3V入力を2.5V出力にレベル・シフト
- デバイスの電源オン時とオフ時の両方で5V許容のI/O
- 伝播遅延がゼロに近い双方向データ・フロー
- 低いオン抵抗(r_{on})特性（r_{on} = 5Ω：標準値）
- 低い入力/出力容量により負荷が最小化（$C_{io(OFF)}$ = 4.5pF：標準値）
- データおよび制御入力にアンダーシュート・クランプ・ダイオードを搭載
- 低い消費電力（I_{CC} = 20μA：最大値）
- 2.3V～3.6Vの範囲のV_{CC}で動作
- データI/Oは0～5Vの信号レベルに対応(0.8V、1.2V、1.5V、1.8V、2.5V、3.3V、5V)
- 制御入力をTTLまたは5V/3.3V CMOS出力で駆動可能
- I_{off}により部分的パワーダウン・モード動作をサポート
- JESD 17準拠で250mA超のラッチアップ性能
- JESD 22準拠でESD性能をテスト済み
  - 人体モデルで2000V (A114-B、クラスII)
  - 荷電デバイス・モデルで1000V (C101)

2 アプリケーション

- デジタル・アプリケーションをサポート：レベル変換、USBインターフェイス、バス分離
- 低消費電力の携帯用機器に理想的

3 概要

SN74CB3T3125は、オン抵抗(r_{on})が低いため伝播遅延を最小限に低減できる高速TTL互換FETバス・スイッチです。このデバイスは、V_{CC}に追従した電圧変換を行うことで、すべてのデータI/Oポートにおいて混在モード信号動作を完全にサポートします。SN74CB3T3125は、5V TTL、3.3V LVTTL、2.5V CMOSスイッチング規格に加えて、ユーザー定義のスイッチング・レベルを使用するシステムに対応します（「*標準的なDC電圧変換特性*」を参照）。

SN74CB3T3125は4つの1ビット・バス・スイッチとして構成され、個別の出力イネーブル($1\overline{OE}$、$2\overline{OE}$、$3\overline{OE}$、$4\overline{OE}$)入力を持っています。このデバイスは、4つの1ビット・バス・スイッチ、または1つの4ビット・バス・スイッチとして使用できます。$\overline{OE}$がLOWのとき、関連付けられている1ビット・バス・スイッチはオンで、AポートはBポートに接続され、ポート間で双方向のデータ・フローが可能になります。$\overline{OE}$をHIGHにすると、関連する1ビット・バス・スイッチはオフになり、AとBのポート間は高インピーダンス状態になります。

このデバイスは、I_{off}を使用する部分的パワーダウン・アプリケーション用に完全に動作が規定されています。I_{off}機能により、パワーダウン時に損傷を引き起こすような電流がデバイスに逆流しないことが保証されます。デバイスは、電源オフ時は絶縁されています。

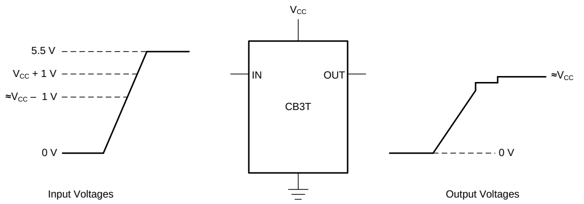
電源オンまたは電源オフ時に高インピーダンス状態を確保するため、$\overline{OE}$はプルアップ抵抗経由でV_{CC}に接続します。この抵抗の最小値は、ドライバの電流シンク能力によって決定されます。

製品情報[1]

型番	パッケージ	本体サイズ(公称)
SN74CB3T3125	VQFN – RGY (14)	3.50mm×3.50mm
	TSSOP – PW (14)	5.00mm×4.40mm
	TVSOP – DGV (14)	3.60mm×4.40mm

(1) 利用可能なすべてのパッケージについては、このデータシートの末尾にある注文情報を参照してください。

標準的なDC電圧変換特性



If the input high voltage (V_{IH}) level is greater than or equal to V_{CC} + 1 V, and less than or equal to 5.5 V, the output high voltage (V_{OH}) level will be equal to approximately the V_{CC} voltage level.

English Data Sheet: SCDS120

目次

4 改訂履歴

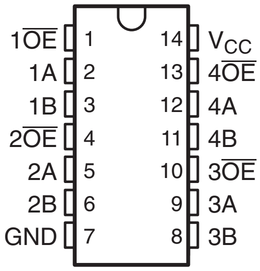
資料番号末尾の英字は改訂を表しています。その改訂履歴は英語版に準じています。

Revision B (August 2012) から Revision C に変更	**Page**
• 「*アプリケーション*」一覧、「*製品情報*」表、「*ESD定格*」表、「*機能説明*」セクション、「*デバイスの機能モード*」セクション、「*アプリケーションと実装*」セクション、「*電源に関する推奨事項*」セクション、「*レイアウト*」セクション、「*デバイスおよびドキュメントのサポート*」セクション、「*メカニカル、パッケージ、および注文情報*」セクションを追加	1
• 「注文情報」表を削除	1
• Changed t_{en} V_{CC} = 3.3 V MAX value From: 4.4 ns To: 8 ns in the *Switching Characteristic*	5

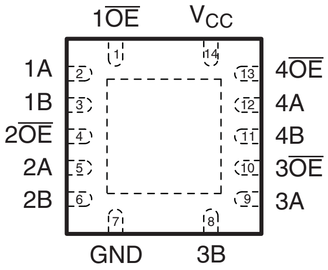
Revision A (April 2009) から Revision B に変更	**Page**
• 「*標準的なDC電圧変換特性*」を更新	1

5 Pin Configuration and Functions

DGV OR PW PACKAGE
(TOP VIEW)



RGY PACKAGE
(TOP VIEW)



Pin Functions

PIN		I/O	DESCRIPTION
NAME	NO.		
1$\overline{\text{OE}}$	1	I	Active-low enable for switch 1
1A	2	I/O	Switch 1 A terminal
1B	3	I/O	Switch 1 B terminal
2$\overline{\text{OE}}$	4	I	Active-low enable for switch 2
2A	5	I/O	Switch 2 A terminal
2B	6	I/O	Switch 2 B terminal
GND	7	-	Ground
3A	8	I/O	Switch 3 A terminal
3B	9	I/O	Switch 3 B terminal
3$\overline{\text{OE}}$	10	I	Active-low enable for switch 3
4A	11	I/O	Switch 4 A terminal
4B	12	I/O	Switch 4 B terminal
4$\overline{\text{OE}}$	13	I	Active-low enable for switch 4
V_{CC}	14	-	Supply voltage pin

6 Specifications

6.1 Absolute Maximum Ratings(1)

over operating free-air temperature range (unless otherwise noted)

			MIN	MAX	UNIT
V_{CC}	Supply voltage range(2)		–0.5	7	V
V_{IN}	Control input voltage range(2) (3)		–0.5	7	V
$V_{I/O}$	Switch I/O voltage range(2) (3) (4)		–0.5	7	V
I_{IK}	Control input clamp current	$V_{IN} < 0$		–50	mA
$I_{I/OK}$	I/O port clamp current	$V_{I/O} < 0$		–50	mA
$I_{I/O}$	ON-state switch current(5)			±128	mA
	Continuous current through V_{CC} or GND			±100	mA
T_{stg}	Storage temperature range		–65	150	°C

(1) Stresses beyond those listed under *Absolute Maximum Ratings* may cause permanent damage to the device. These are stress ratings only, which do not imply functional operation of the device at these or any other conditions beyond those indicated under *Recommended Operating Conditions*. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.
(2) All voltages are with respect to ground unless otherwise specified.
(3) The input and output voltage ratings may be exceeded if the input and output clamp-current ratings are observed.
(4) V_I and V_O are used to denote specific conditions for $V_{I/O}$.
(5) I_I and I_O are used to denote specific conditions for $I_{I/O}$.

6.2 ESD Ratings

			VALUE	UNIT
$V_{(ESD)}$	Electrostatic discharge	Human-body model (HBM), per ANSI/ESDA/JEDEC JS-001(1)	±2000	V
		Charged-device model (CDM), per JEDEC specification JESD22-C101(2)	±1000	

(1) JEDEC document JEP155 states that 500-V HBM allows safe manufacturing with a standard ESD control process..
(2) JEDEC document JEP157 states that 250-V CDM allows safe manufacturing with a standard ESD control process.

6.3 Recommended Operating Conditions(1)

			MIN	MAX	UNIT
V_{CC}	Supply voltage		2.3	3.6	V
V_{IH}	High-level control input voltage	V_{CC} = 2.3 V to 2.7 V	1.7	5.5	V
		V_{CC} = 2.7 V to 3.6 V	2	5.5	
V_{IL}	Low-level control input voltage	V_{CC} = 2.3 V to 2.7 V	0	0.7	V
		V_{CC} = 2.7 V to 3.6 V	0	0.8	
$V_{I/O}$	Data input/output voltage		0	5.5	V
T_A	Operating free-air temperature		–40	85	°C

(1) All unused control inputs of the device must be held at V_{CC} or GND to ensure proper device operation. Refer to the TI application report, *Implications of Slow or Floating CMOS Inputs*, literature number SCBA004.

6.4 Thermal Information

THERMAL METRIC(1)		SN74CB3T3125			UNIT
		VQFN (RGY)	TSSOP (PW)	TVSOP (DGV)	
		14 PINS	14 PINS	14 PINS	
$R_{\theta JA}$	Junction-to-ambient thermal resistance	55.5	123.3	154.8	°C/W
$R_{\theta JC(top)}$	Junction-to-case (top) thermal resistance	56.9	53.0	64.4	°C/W
$R_{\theta JB}$	Junction-to-board thermal resistance	30.9	66.3	88.4	°C/W
ψ_{JT}	Junction-to-top characterization parameter	3.6	9.1	10.8	°C/W
ψ_{JB}	Junction-to-board characterization parameter	30.9	65.7	87.4	°C/W
$R_{\theta JC(bot)}$	Junction-to-case (bottom) thermal resistance	14.6	-	-	°C/W

(1) For more information about traditional and new thermal metrics, see the *Semiconductor and IC Package Thermal Metrics* application report.

6.5 Electrical Characteristics[1]

over recommended operating free-air temperature range (unless otherwise noted)

PARAMETER		TEST CONDITIONS		MIN	TYP[2]	MAX	UNIT
V_{IK}		V_{CC} = 3 V, I_I = –18 mA				–1.2	V
V_{OH}		See Figure 3 through Figure 5					
I_{IN}	Control inputs	V_{CC} = 3.6 V, V_{IN} = 3.6 V to 5.5 V or GND				±10	μA
I_I		V_{CC} = 3.6 V, Switch ON, V_{IN} = V_{CC} or GND	V_I = V_{CC} – 0.7 V to 5.5 V			±20	μA
			V_I = 0.7 V to V_{CC} – 0.7 V			–40	
			V_I = 0 to 0.7 V			±5	
I_{OZ} [3]		V_{CC} = 3.6 V, V_O = 0 to 5.5 V, V_I = 0, Switch OFF, V_{IN} = V_{CC} or GND				±10	μA
I_{off}		V_{CC} = 0, V_O = 0 to 5.5 V, V_I = 0				10	μA
I_{CC}		V_{CC} = 3.6 V, $I_{I/O}$ = 0, Switch ON or OFF, V_{IN} = V_{CC} or GND	V_I = V_{CC} or GND			20	μA
			V_I = 5.5 V			20	
ΔI_{CC} [4]	Control inputs	V_{CC} = 3 V to 3.6 V, One input at V_{CC} – 0.6 V, Other inputs at V_{CC} or GND				300	μA
C_{in}	Control inputs	V_{CC} = 3.3 V, V_{IN} = V_{CC} or GND			3		pF
$C_{io(OFF)}$		V_{CC} = 3.3 V, $V_{I/O}$ = 5.5 V, 3.3 V, or GND, Switch OFF, V_{IN} = V_{CC} or GND			4.5		pF
$C_{io(ON)}$		V_{CC} = 3.3 V, Switch ON, V_{IN} = V_{CC} or GND	$V_{I/O}$ = 5.5 V or 3.3 V		4		pF
			$V_{I/O}$ = GND		10		
r_{on} [5]		V_{CC} = 2.3 V, TYP at V_{CC} = 2.5 V, V_I = 0	I_O = 24 mA		5	8	Ω
			I_O = 16 mA		5	8	
		V_{CC} = 3 V, V_I = 0	I_O = 64 mA		5	7	
			I_O = 32 mA		5	7	

(1) V_{IN} and I_{IN} refer to control inputs. V_I, V_O, I_I, and I_O refer to data pins.
(2) All typical values are at V_{CC} = 3.3 V (unless otherwise noted), T_A = 25°C.
(3) For I/O ports, the parameter I_{OZ} includes the input leakage current.
(4) This is the increase in supply current for each input that is at the specified TTL voltage level, rather than V_{CC} or GND.
(5) Measured by the voltage drop between A and B terminals at the indicated current through the switch. ON-state resistance is determined by the lower of the voltages of the two (A or B) terminals.

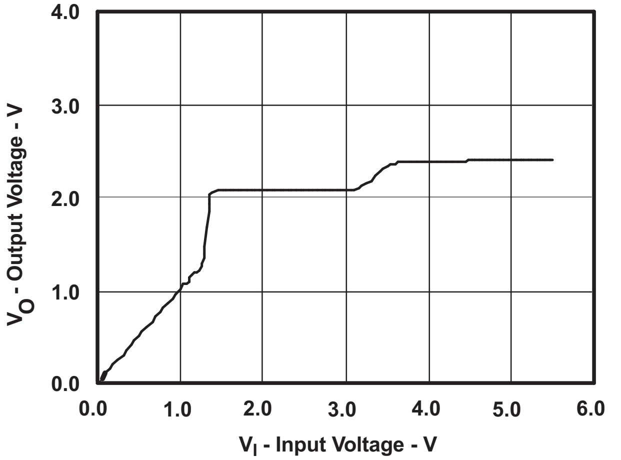
6.6 Switching Characteristics

over recommended operating free-air temperature range (unless otherwise noted) (see Figure 6)

PARAMETER	FROM (INPUT)	TO (OUTPUT)	V_{CC} = 2.5 V ± 0.2 V		V_{CC} = 3.3 V ± 0.3 V		UNIT
			MIN	MAX	MIN	MAX	
t_{pd} [1]	A or B	B or A		0.15		0.25	ns
t_{en}	$\overline{OE}$	A or B	1	8.5	1	8	ns
t_{dis}	$\overline{OE}$	A or B	1	9	1	9	ns

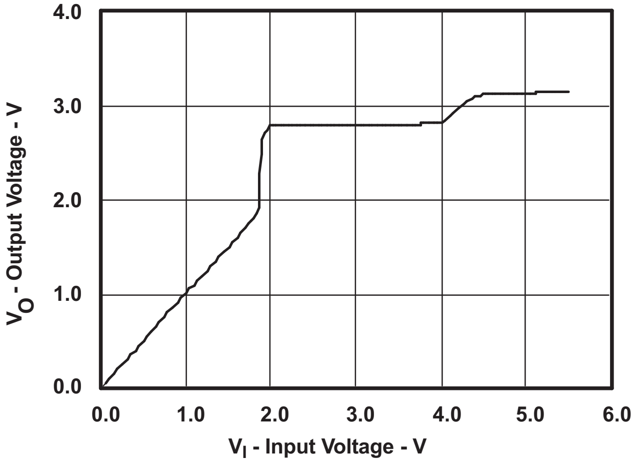
(1) The propagation delay is the calculated RC time constant of the typical ON-state resistance of the switch and the specified load capacitance, when driven by an ideal voltage source (zero output impedance).

6.7 Typical Characteristics



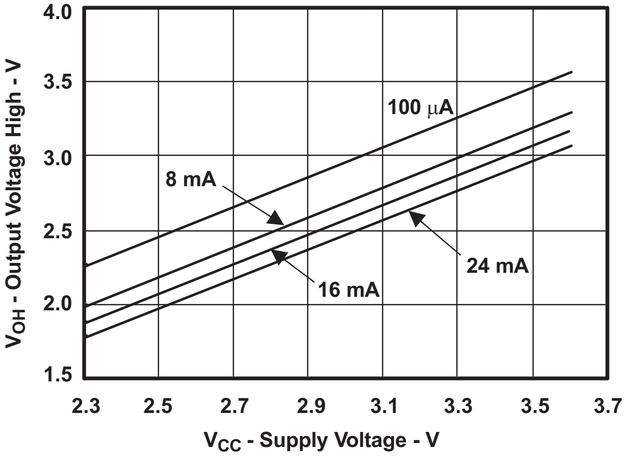
V_{CC} = 2.3 V I_O = 1 µA T_A = 25°C

Figure 1. Data Output Voltage vs Data Input Voltage



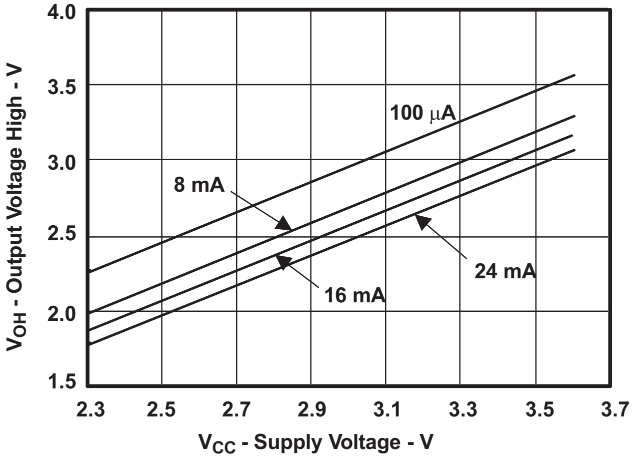
V_{CC} = 3 V I_O = 1 µA T_A = 25°C

Figure 2. Data Output Voltage vs Data Input Voltage



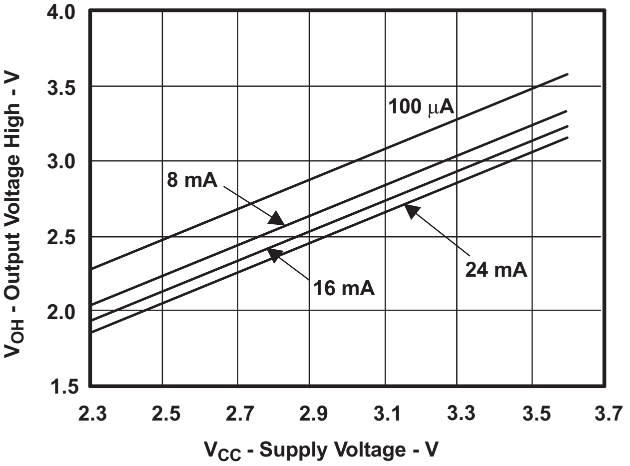
V_{CC} = 2.3 V to 3.6 V V_I = 5.5 V T_A = 85°C

Figure 3. Output Voltage High vs Supply Voltage



V_{CC} = 2.3 V to 3.6 V V_I = 5.5 V T_A = 25°C

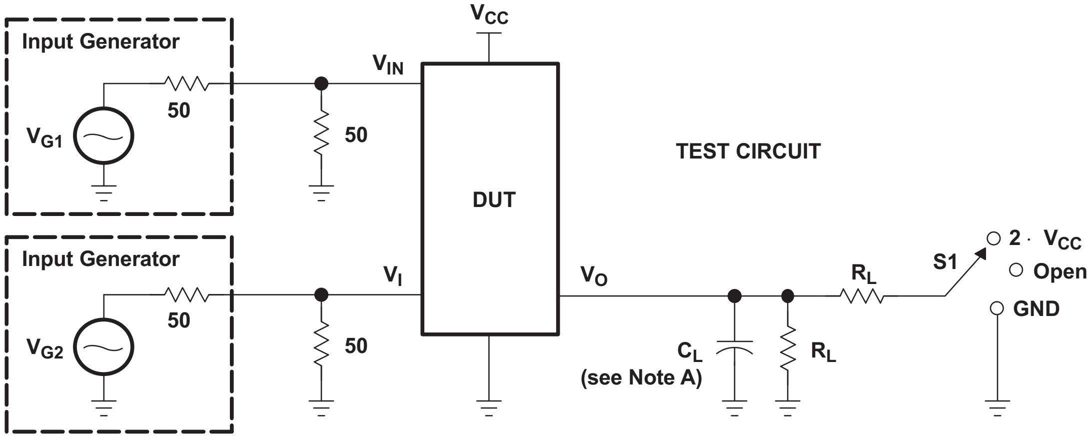
Figure 4. Output Voltage High vs Supply Voltage



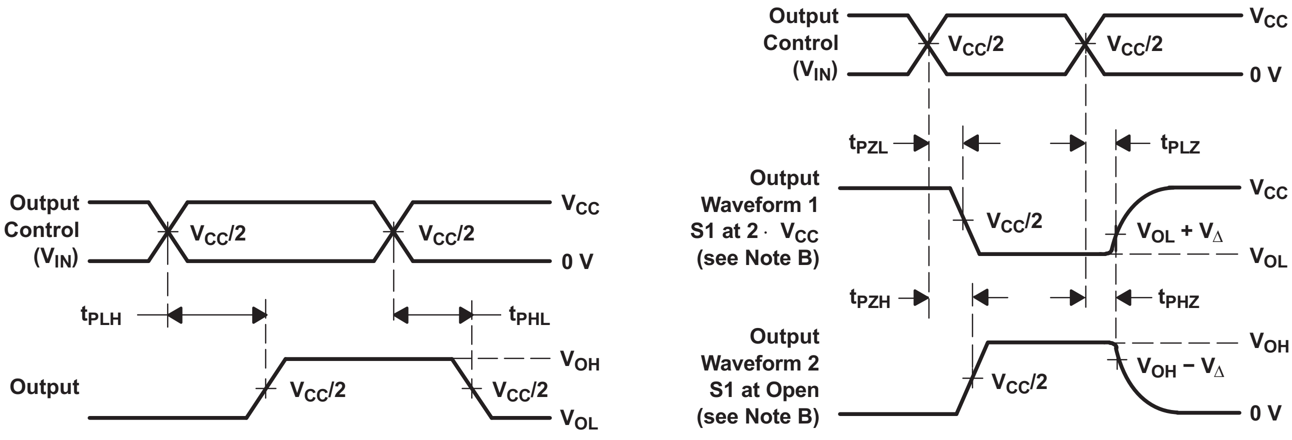
V_{CC} = 2.3 V to 3.6 V V_I = 5.5 V T_A = -40°C

Figure 5. Output Voltage High vs Supply Voltage

7 Parameter Measurement Information



TEST	V_{CC}	S1	R_L	V_I	C_L	V
$t_{pd(s)}$	2.5 V ± 0.2 V 3.3 V ± 0.3 V	Open Open	500 500	3.6 V or GND 5.5 V or GND	30 pF 50 pF	
t_{PLZ}/t_{PZL}	2.5 V ± 0.2 V 3.3 V ± 0.3 V	2 · V_{CC} 2 · V_{CC}	500 500	GND GND	30 pF 50 pF	0.15 V 0.3 V
t_{PHZ}/t_{PZH}	2.5 V ± 0.2 V 3.3 V ± 0.3 V	Open Open	500 500	3.6 V 5.5 V	30 pF 50 pF	0.15 V 0.3 V



VOLTAGE WAVEFORMS
PROPAGATION DELAY TIMES ($t_{pd(s)}$)

VOLTAGE WAVEFORMS
ENABLE AND DISABLE TIMES

NOTES:
- A. C_L includes probe and jig capacitance.
- B. Waveform 1 is for an output with internal conditions such that the output is low, except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high, except when disabled by the output control.
- C. All input pulses are supplied by generators having the following characteristics: PRR 10 MHz, Z_O = 50 Ω, t_r 2.5 ns, t_f 2.5 ns.
- D. The outputs are measured one at a time, with one transition per measurement.
- E. t_{PLZ} and t_{PHZ} are the same as t_{dis}.
- F. t_{PZL} and t_{PZH} are the same as t_{en}.
- G. t_{PLH} and t_{PHL} are the same as $t_{pd(s)}$. The tpd propagation delay is the calculated RC time constant of the typical ON-state resistance of the switch and the specified load capacitance, when driven by an ideal voltage source (zero output impedance).
- H. All parameters and waveforms are not applicable to all devices.

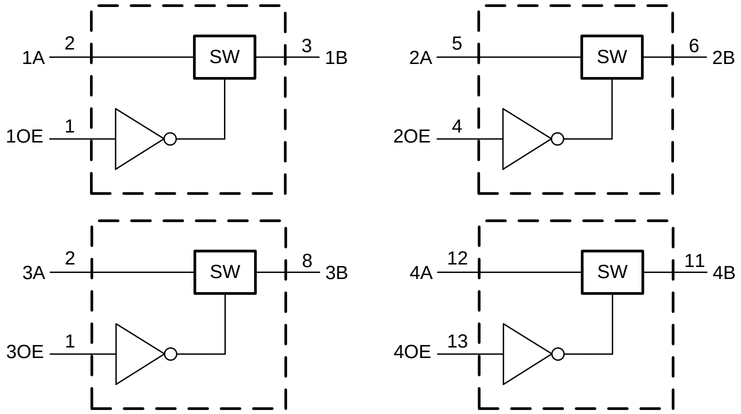
Figure 6. Test Circuit and Voltage Waveforms

8 Detailed Description

8.1 Overview

The SN74CB3T3215 device is organized as four 1-bit bus switches with separate ouput-enable (1OE, 2OE, 3OE, and 4 OE) inputs. When OE is low, the associated 1-bit bus switch is ON, and the A port is connected to the B port, allowing bidirectional data flow between ports. When OE is high, the associated 1-bit bus switch is OFF, and a high-impedance state exists between the A and B ports. This device is fully specified for partial-power-down applications using Ioff. The Ioff feature ensures that damaging current will not backflow through the device when it is powered down. The SN74CB3T3125 device has isolation during power off. To ensure the high-impedance state during power up or power down, OE should be tied to VCC through a pullup resistor; the minimum value of the resistor is determined by the current-sinking capability of the driver.

8.2 Functional Block Diagram



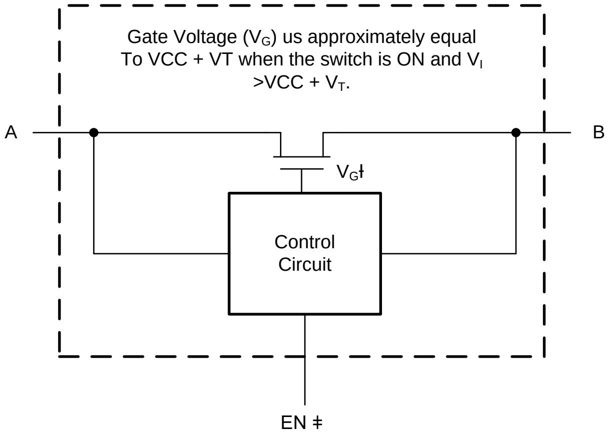


Figure 7. Simplified Schematic, Each FET Switch (SW)

8.3 Feature Description

The SN74CB3T3125 is ideal for low-power portable equipment. Power consumption is low by design, I_{CC} = 20 µA, On-state resistance is low (r_{on} = 5 Ω) It has bidirectional data flow with near zero propagation delay. The devices minimizes loading due to the low input/output capacitance $C_{io(OFF)}$ = 4.5 pF Typical. Operating VCC range from 2.3 V to 3.6 V. The output tracks VCC. Data and control inputs provide undershoot clamp diodes. Control inputs can be driven by TTL or 5-V/3.3-V CMOS outputs. It supports mixed-mode signal operation on all data I/O ports. Data I/Os support 0- to 5-V signaling levels (0.8 V, 1.2 V, 1.5 V, 1.8 V, 2.5 V, 3.3 V, 5 V). The device is protected from damaging current, Ioff supports partial shutdown which prevents the current from flowing back through the device when it is powered down. In addition, it has 5-V tolerant I/Os with device powered up or powered down. The device is latch-up resistant with 250 mA exceeding the JESD 17 standard, providing protection from destruction due to latch-up. This device is protected against electrostatic discharge. It is tested per JESD 22 using 2000-V Human-Body Model (A114-B, Class II), and 1000-V Charged-Device Model (C101).

8.4 Device Functional Modes

Table 1 lists the functional modes for the SN74CB3T3125.

Table 1. Function Table (Each Bus Switch)

INPUT $\overline{\text{OE}}$	INPUT/OUTPUT A	FUNCTION
L	B	A port = B port
H	Z	Disconnect

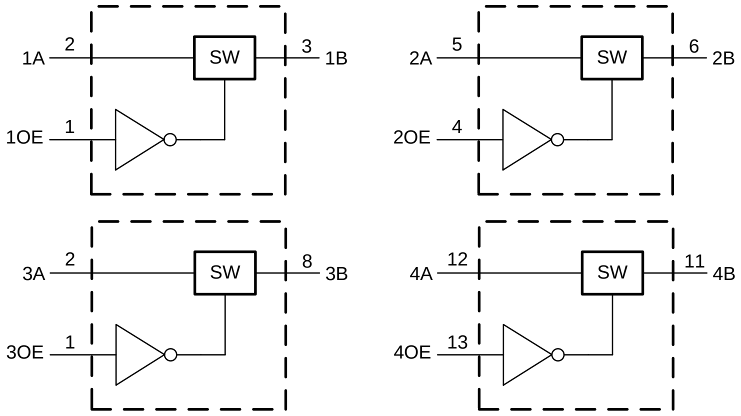


Figure 8. Logic Diagram (Positive Logic)

9 Application and Implementation

NOTE

Information in the following applications sections is not part of the TI component specification, and TI does not warrant its accuracy or completeness. TI's customers are responsible for determining suitability of components for their purposes. Customers should validate and test their design implementation to confirm system functionality.

9.1 Application Information

This application is specifically to connect a 5-V bus to a 3.3 V device. Ideally, set VCC to 3.3 V. It is assumed that communication in this particular application is one-directional, going from the bus controller to the device.

9.2 Typical Application

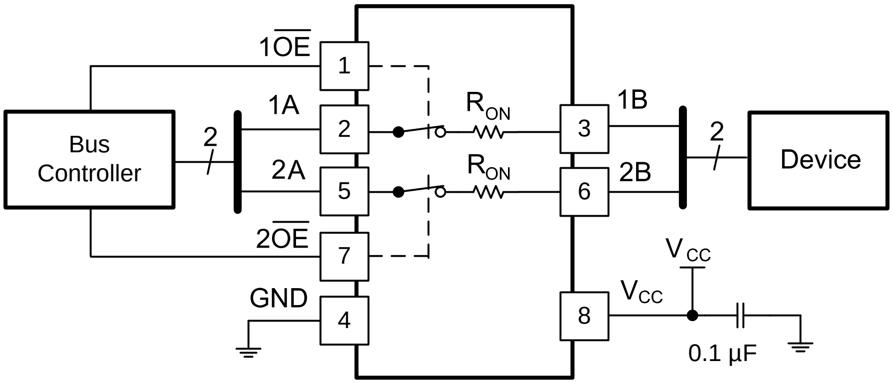


Figure 9. Application Circuit

9.2.1 Design Requirements

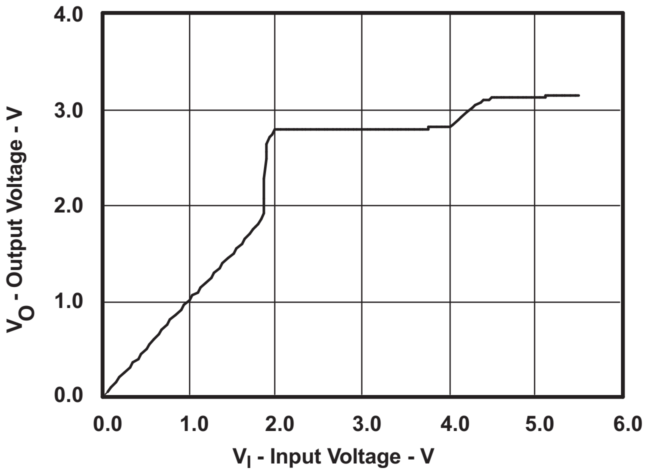
This device uses CMOS technology and has balanced output drive. Take care to avoid bus contention because it can drive currents that would exceed maximum limits. Because this design is for down-translating voltage, no pull-up resistors are required.

9.2.2 Detailed Design Procedure

1. Recommended Input conditions – Specified high and low levels. See (V_{IH} and V_{IL}) in *Recommended Operating Conditions* – Inputs are overvoltage tolerant allowing them to go as high as 7 V at any valid VCC.
2. Recommend output conditions – Load currents should not exceed 128 mA on each channel.

Typical Application (continued)

9.2.3 Application Curves



$V_{CC} = 3$ V $I_O = 1$ µA $T_A = 25$°C

Figure 10. Data Output Voltage vs Data Input Voltage

10 Power Supply Recommendations

The power supply can be any voltage between the minimum and maximum supply voltage rating located in the Recommended Operating Conditions.

Each VCC terminal should have a good bypass capacitor to prevent power disturbance. For devices with a single supply, a 0.1-µF bypass capacitor is recommended. If there are multiple pins labeled VCC, then a 0.01-µF or 0.022-µF capacitor is recommended for each VCC because the VCC pins will be tied together internally. For devices with dual supply pins operating at different voltages, for example VCC and VDD, a 0.1-µF bypass capacitor is recommended for each supply pin. It is acceptable to parallel multiple bypass capacitors to reject different frequencies of noise. 0.1-µF and 1-µF capacitors are commonly used in parallel. The bypass capacitor should be installed as close to the power terminal as possible for best results.

11 Layout

11.1 Layout Guidelines

Reflections and matching are closely related to the loop antenna theory but are different enough to be discussed separately from the theory. When a PCB trace turns a corner at a 90° angle, a reflection can occur. A reflection occurs primarily because of the change of width of the trace. At the apex of the turn, the trace width increases to 1.414 times the width. This increase upsets the transmission-line characteristics, especially the distributed capacitance and self–inductance of the trace which results in the reflection. Not all PCB traces can be straight and therefore some traces must turn corners. Figure 11 shows progressively better techniques of rounding corners. Only the last example (BEST) maintains constant trace width and minimizes reflections.

11.2 Layout Example

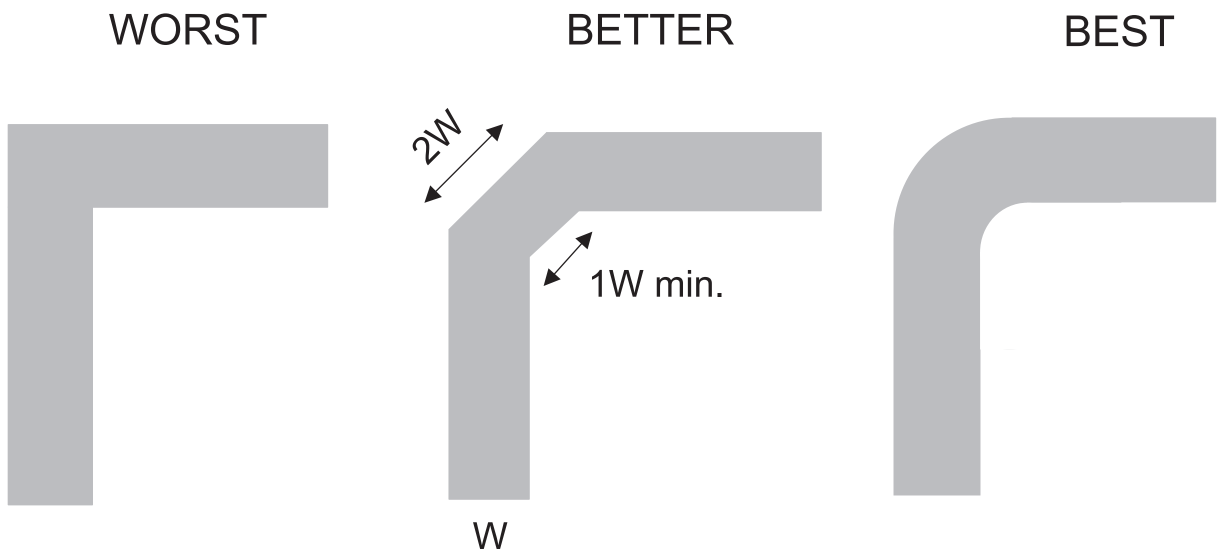


Figure 11. Example Layout

12 デバイスおよびドキュメントのサポート

12.1 デバイス・サポート

12.2 ドキュメントの更新通知を受け取る方法

ドキュメントの更新についての通知を受け取るには、ti.comのデバイス製品フォルダを開いてください。右上の「アラートを受け取る」をクリックして登録すると、変更されたすべての製品情報に関するダイジェストを毎週受け取れます。変更の詳細については、修正されたドキュメントに含まれている改訂履歴をご覧ください。

12.3 コミュニティ・リソース

The following links connect to TI community resources. Linked contents are provided "AS IS" by the respective contributors. They do not constitute TI specifications and do not necessarily reflect TI's views; see TI's Terms of Use.

TI E2E™オンライン・コミュニティ ***TIのE2E（Engineer-to-Engineer）***コミュニティ。エンジニア間の共同作業を促進するために開設されたものです。e2e.ti.comでは、他のエンジニアに質問し、知識を共有し、アイディアを検討して、問題解決に役立てることができます。

設計サポート ***TIの設計サポート*** 役に立つE2Eフォーラムや、設計サポート・ツールをすばやく見つけることができます。技術サポート用の連絡先情報も参照できます。

12.4 商標

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All other trademarks are the property of their respective owners.

12.5 静電気放電に関する注意事項

すべての集積回路は、適切なESD保護方法を用いて、取扱いと保存を行うようにして下さい。

静電気放電はわずかな性能の低下から完全なデバイスの故障に至るまで、様々な損傷を与えます。高精度の集積回路は、損傷に対して敏感であり、極めてわずかなパラメータの変化により、デバイスに規定された仕様に適合しなくなる場合があります。

12.6 Glossary

SLYZ022 — *TI Glossary*.

This glossary lists and explains terms, acronyms, and definitions.

13 メカニカル、パッケージ、および注文情報

以降のページには、メカニカル、パッケージ、および注文に関する情報が記載されています。この情報は、そのデバイスについて利用可能な最新のデータです。このデータは予告なく変更されることがあり、ドキュメントが改訂される場合もあります。本データシートのブラウザ版を使用されている場合は、画面左側の説明をご覧ください。

PACKAGE OPTION ADDENDUM

PACKAGING INFORMATION

Orderable Device	Status (1)	Package Type	Package Drawing	Pins	Package Qty	Eco Plan (2)	Lead finish/ Ball material (6)	MSL Peak Temp (3)	Op Temp (°C)	Device Marking (4/5)	Samples
SN74CB3T3125DGVR	ACTIVE	TVSOP	DGV	14	2000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 85	KS125	Samples
SN74CB3T3125PW	LIFEBUY	TSSOP	PW	14	90	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 85	KS125	
SN74CB3T3125PWR	ACTIVE	TSSOP	PW	14	2000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 85	KS125	Samples
SN74CB3T3125PWRE4	LIFEBUY	TSSOP	PW	14	2000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 85	KS125	
SN74CB3T3125RGYR	ACTIVE	VQFN	RGY	14	3000	RoHS & Green	NIPDAU	Level-2-260C-1 YEAR	-40 to 85	KS125	Samples

(1) The marketing status values are defined as follows:
ACTIVE: Product device recommended for new designs.
LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.
NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.
PREVIEW: Device has been announced but is not in production. Samples may or may not be available.
OBSOLETE: TI has discontinued the production of the device.

(2) **RoHS:** TI defines "RoHS" to mean semiconductor products that are compliant with the current EU RoHS requirements for all 10 RoHS substances, including the requirement that RoHS substance do not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, "RoHS" products are suitable for use in specified lead-free processes. TI may reference these types of products as "Pb-Free".
RoHS Exempt: TI defines "RoHS Exempt" to mean products that contain lead but are compliant with EU RoHS pursuant to a specific EU RoHS exemption.
Green: TI defines "Green" to mean the content of Chlorine (Cl) and Bromine (Br) based flame retardants meet JS709B low halogen requirements of <=1000ppm threshold. Antimony trioxide based flame retardants must also meet the <=1000ppm threshold requirement.

(3) MSL, Peak Temp. - The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

(4) There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.

(5) Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.

(6) Lead finish/Ball material - Orderable Devices may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.

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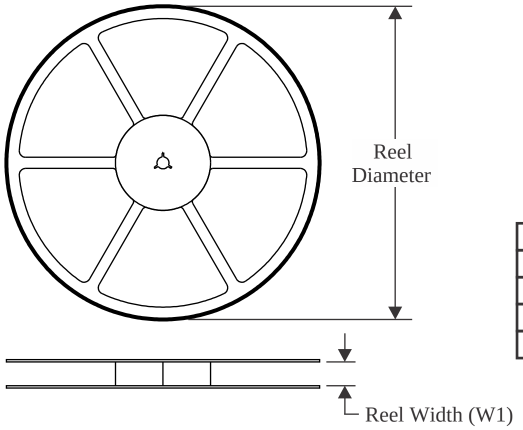
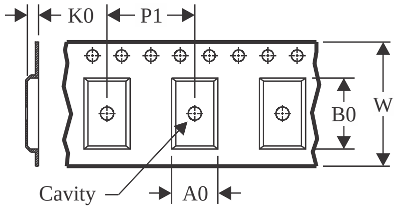
In no event shall TI's liability arising out of such information exceed the total purchase price of the TI part(s) at issue in this document sold by TI to Customer on an annual basis.

TAPE AND REEL INFORMATION

REEL DIMENSIONS

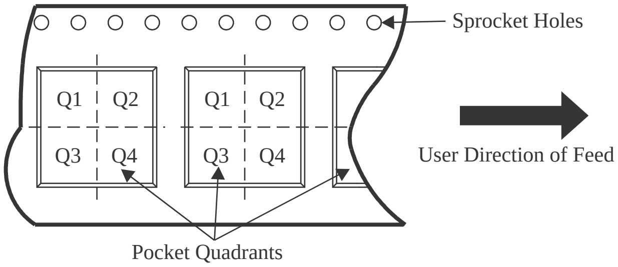


TAPE DIMENSIONS



A0	Dimension designed to accommodate the component width
B0	Dimension designed to accommodate the component length
K0	Dimension designed to accommodate the component thickness
W	Overall width of the carrier tape
P1	Pitch between successive cavity centers

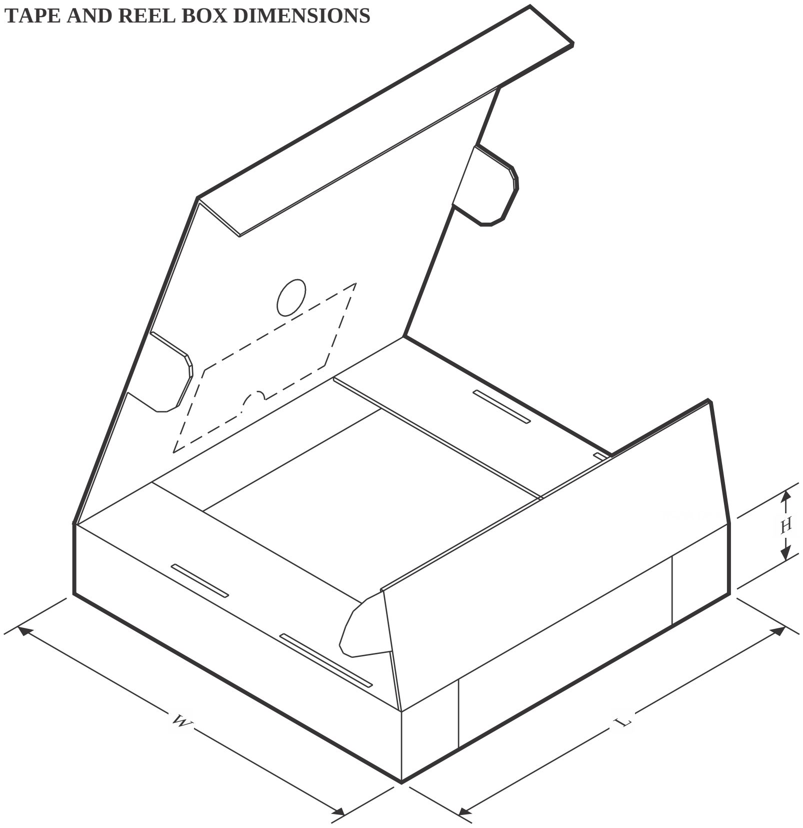
QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE



*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
SN74CB3T3125DGVR	TVSOP	DGV	14	2000	330.0	12.4	6.8	4.0	1.6	8.0	12.0	Q1
SN74CB3T3125PWR	TSSOP	PW	14	2000	330.0	12.4	6.9	5.6	1.6	8.0	12.0	Q1
SN74CB3T3125RGYR	VQFN	RGY	14	3000	330.0	12.4	3.75	3.75	1.15	8.0	12.0	Q1

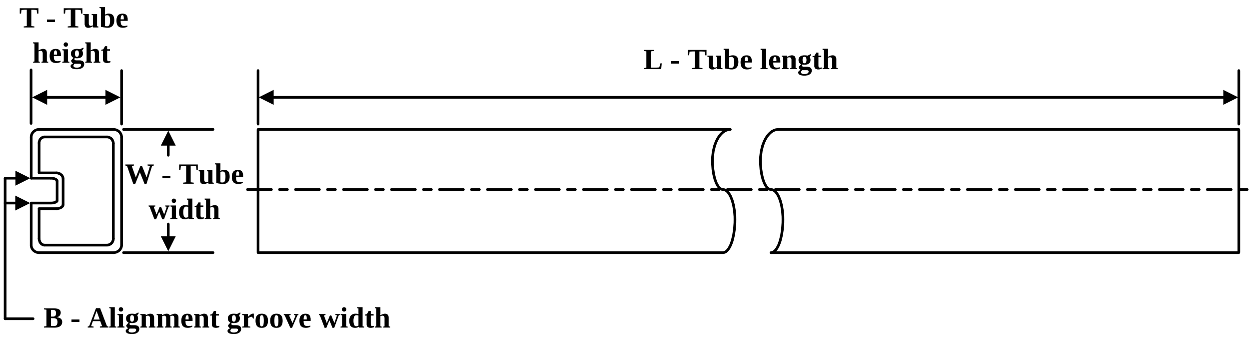
TAPE AND REEL BOX DIMENSIONS



*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
SN74CB3T3125DGVR	TVSOP	DGV	14	2000	367.0	367.0	35.0
SN74CB3T3125PWR	TSSOP	PW	14	2000	367.0	367.0	35.0
SN74CB3T3125RGYR	VQFN	RGY	14	3000	367.0	367.0	35.0

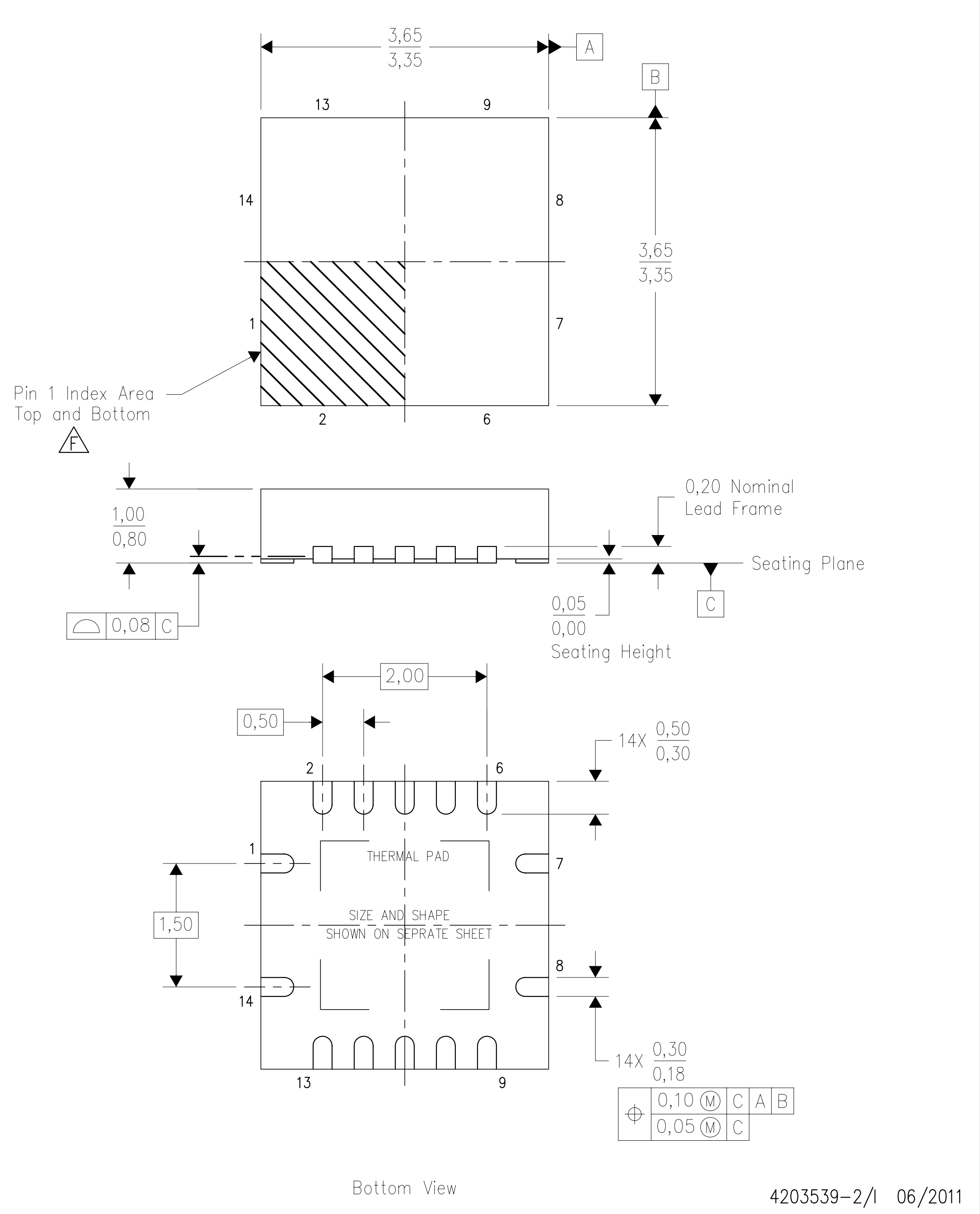
TUBE



*All dimensions are nominal

Device	Package Name	Package Type	Pins	SPQ	L (mm)	W (mm)	T (µm)	B (mm)
SN74CB3T3125PW	PW	TSSOP	14	90	530	10.2	3600	3.5

RGY (S-PVQFN-N14) PLASTIC QUAD FLATPACK NO-LEAD



NOTES:
- A. All linear dimensions are in millimeters. Dimensioning and tolerancing per ASME Y14.5M–1994.
- B. This drawing is subject to change without notice.
- C. QFN (Quad Flatpack No–Lead) package configuration.
- D. The package thermal pad must be soldered to the board for thermal and mechanical performance.
- E. See the additional figure in the Product Data Sheet for details regarding the exposed thermal pad features and dimensions.
- △F Pin 1 identifiers are located on both top and bottom of the package and within the zone indicated. The Pin 1 identifiers are either a molded, marked, or metal feature.
- G. Package complies to JEDEC MO–241 variation BA.

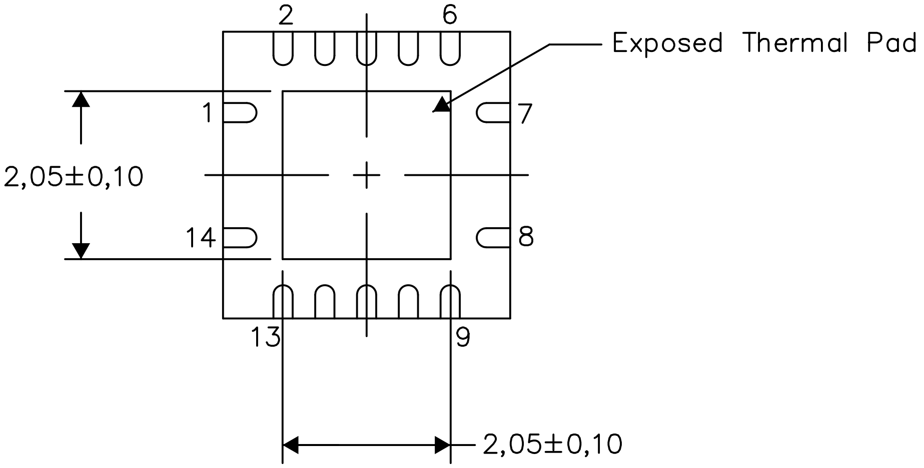
RGY (S–PVQFN–N14) PLASTIC QUAD FLATPACK NO–LEAD

THERMAL INFORMATION

This package incorporates an exposed thermal pad that is designed to be attached directly to an external heatsink. The thermal pad must be soldered directly to the printed circuit board (PCB). After soldering, the PCB can be used as a heatsink. In addition, through the use of thermal vias, the thermal pad can be attached directly to the appropriate copper plane shown in the electrical schematic for the device, or alternatively, can be attached to a special heatsink structure designed into the PCB. This design optimizes the heat transfer from the integrated circuit (IC).

For information on the Quad Flatpack No–Lead (QFN) package and its advantages, refer to Application Report, QFN/SON PCB Attachment, Texas Instruments Literature No. SLUA271. This document is available at www.ti.com.

The exposed thermal pad dimensions for this package are shown in the following illustration.



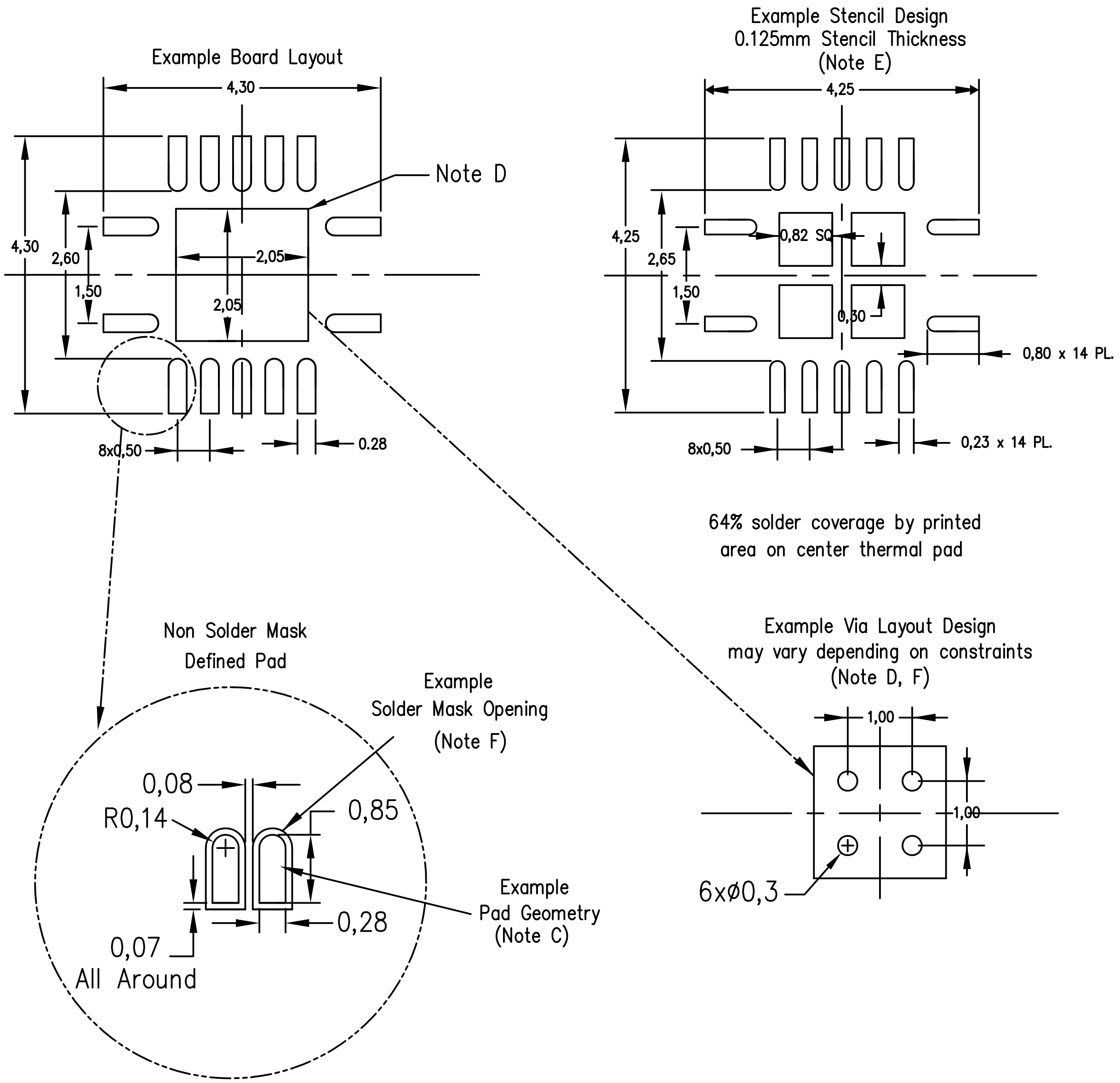
Bottom View

Exposed Thermal Pad Dimensions

4206353–2/P 03/14

NOTE: All linear dimensions are in millimeters

RGY (S-PVQFN-N14) PLASTIC QUAD FLATPACK NO-LEAD

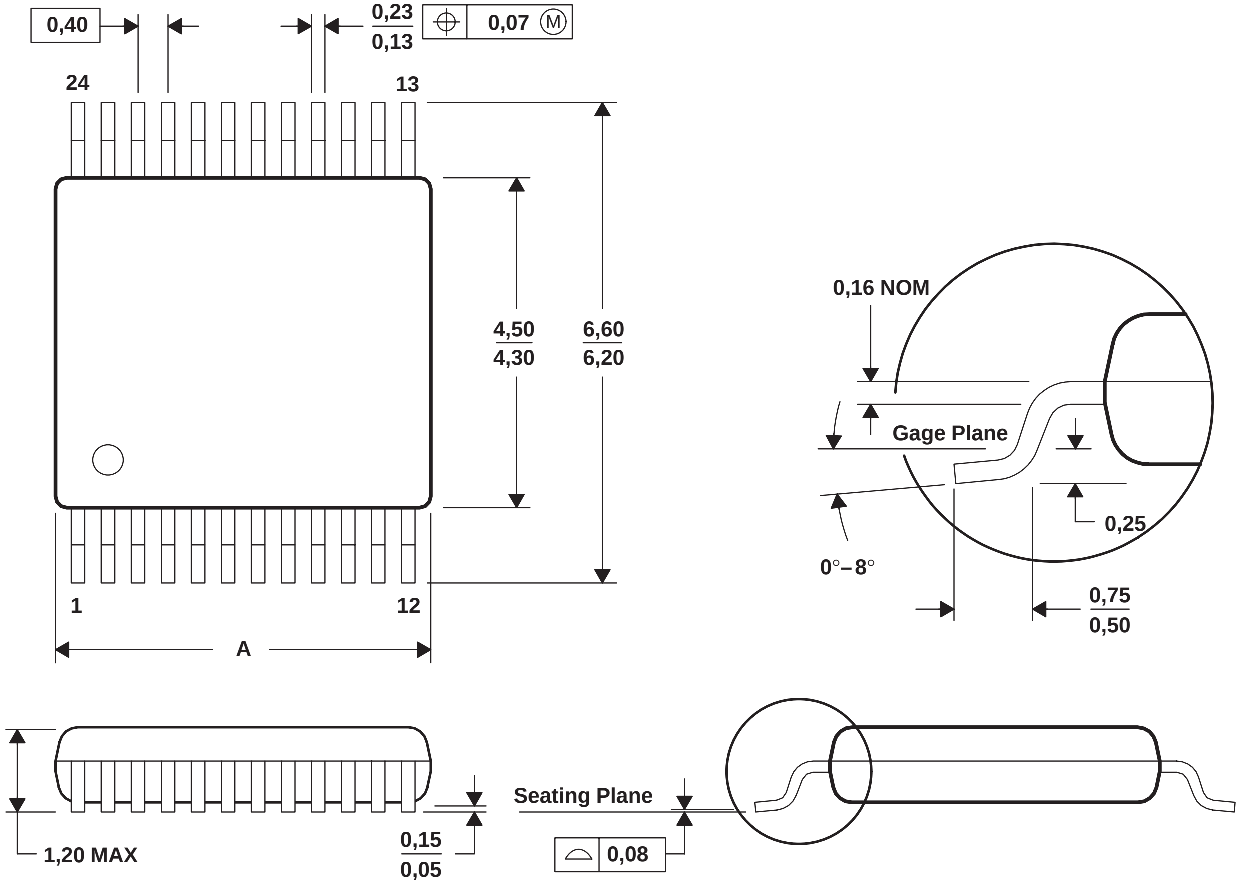


4208122-2/P 03/14

NOTES:
- A. All linear dimensions are in millimeters.
- B. This drawing is subject to change without notice.
- C. Publication IPC-7351 is recommended for alternate designs.
- D. This package is designed to be soldered to a thermal pad on the board. Refer to Application Note, Quad Flat-Pack QFN/SON PCB Attachment, Texas Instruments Literature No. SLUA271, and also the Product Data Sheets for specific thermal information, via requirements, and recommended board layout. These documents are available at www.ti.com <http://www.ti.com>.
- E. Laser cutting apertures with trapezoidal walls and also rounding corners will offer better paste release. Customers should contact their board assembly site for stencil design recommendations. Refer to IPC 7525 for stencil design considerations.
- F. Customers should contact their board fabrication site for minimum solder mask web tolerances between signal pads.

DGV (R-PDSO-G)** **PLASTIC SMALL-OUTLINE**

24 PINS SHOWN

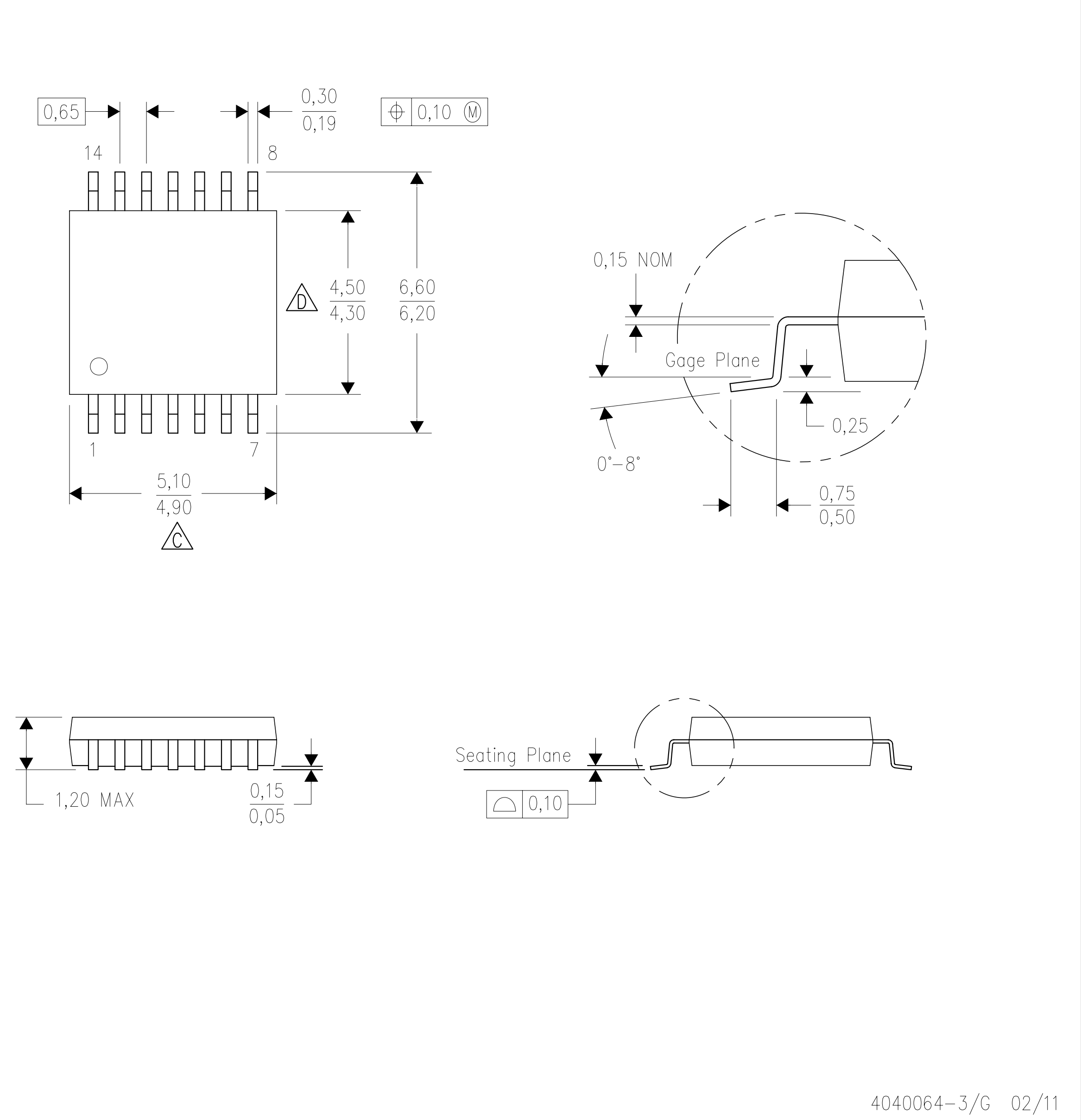


PINS ** / DIM	14	16	20	24	38	48	56
A MAX	3,70	3,70	5,10	5,10	7,90	9,80	11,40
A MIN	3,50	3,50	4,90	4,90	7,70	9,60	11,20

4073251/E 08/00

NOTES:
- A. All linear dimensions are in millimeters.
- B. This drawing is subject to change without notice.
- C. Body dimensions do not include mold flash or protrusion, not to exceed 0,15 per side.
- D. Falls within JEDEC: 24/48 Pins – MO-153
  14/16/20/56 Pins – MO-194

PW (R-PDSO-G14) PLASTIC SMALL OUTLINE



NOTES:

A. All linear dimensions are in millimeters. Dimensioning and tolerancing per ASME Y14.5M–1994.

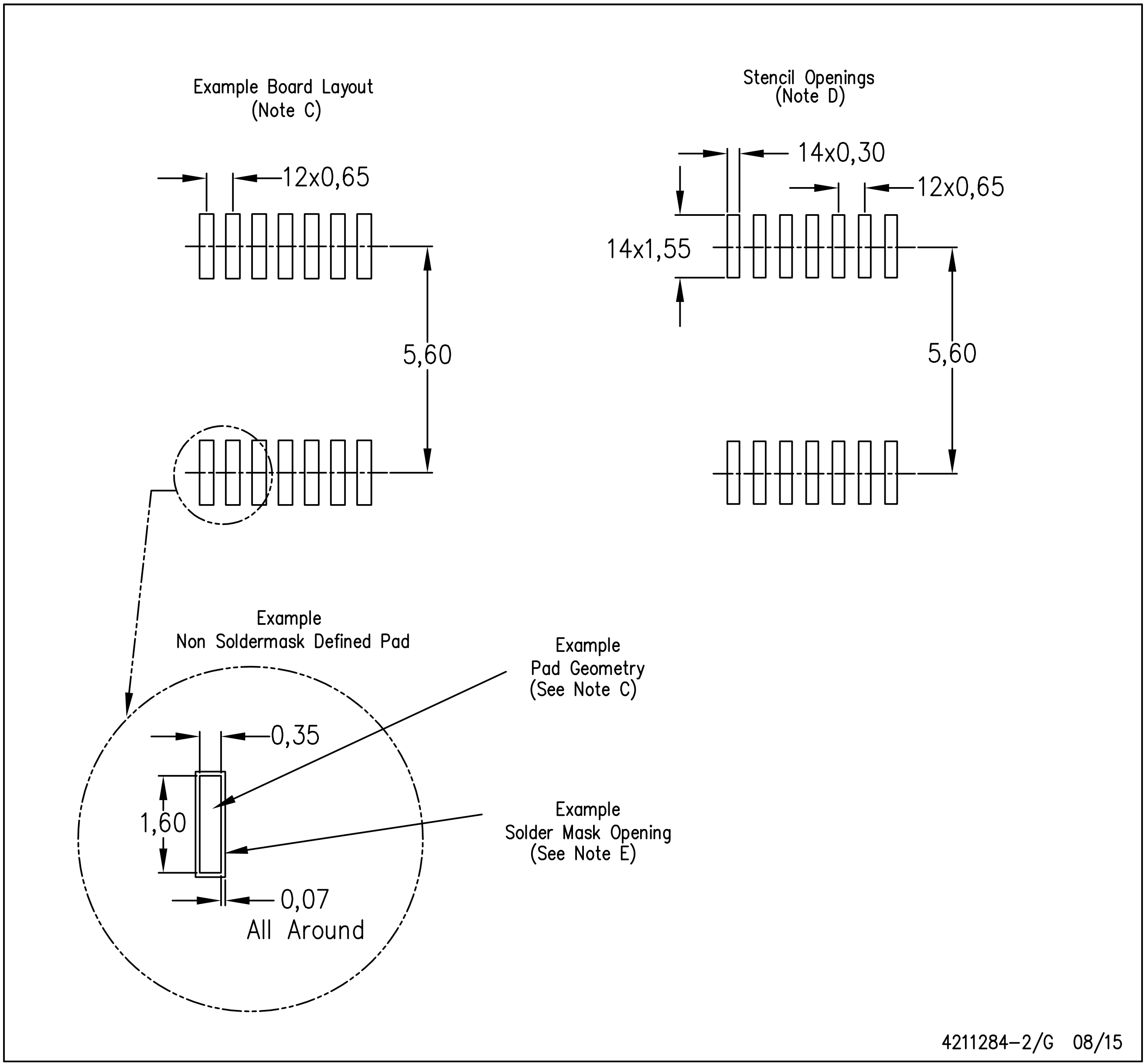
B. This drawing is subject to change without notice.

C. Body length does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed 0,15 each side.

D. Body width does not include interlead flash. Interlead flash shall not exceed 0,25 each side.

E. Falls within JEDEC MO–153

PW (R-PDSO-G14) PLASTIC SMALL OUTLINE



NOTES:
- A. All linear dimensions are in millimeters.
- B. This drawing is subject to change without notice.
- C. Publication IPC-7351 is recommended for alternate designs.
- D. Laser cutting apertures with trapezoidal walls and also rounding corners will offer better paste release. Customers should contact their board assembly site for stencil design recommendations. Refer to IPC-7525 for other stencil recommendations.
- E. Customers should contact their board fabrication site for solder mask tolerances between and around signal pads.

重要なお知らせと免責事項

郵送先住所：Texas Instruments, Post Office Box 655303, Dallas, Texas 75265